

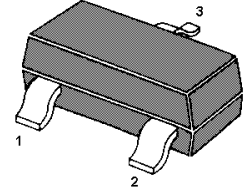
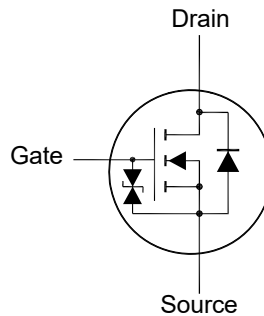
MMFTN6001K

N-Channel Enhancement Mode MOSFET

Features

- Built-in G-S Protection Diode
- Typical ESD Protection HBM Class 2

Classification	Voltage Range(V)
0A	< 125
0B	125 to < 250
1A	250 to < 500
1B	500 to < 1000
1C	1000 to < 2000
2	2000 to < 4000
3A	4000 to < 8000
3B	≥ 8000



1. Gate 2. Source 3. Drain
SOT-23 Plastic Package

Application

- Portable appliances
- Battery management

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

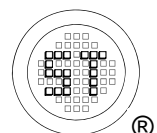
Parameter	Symbol	Value	Unit
Drain Source Voltage	V_{DS}	60	V
Gate Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	440	mA
Peak Drain Current, Pulsed ¹⁾	I_{DM}	1	A
Power Dissipation ²⁾	P_{tot}	530	mW
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Resistance Ratings

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient ²⁾ $t \leq 10$ s Steady State	$R_{\theta JA}$	180 235	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$.

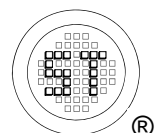
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.



MMFTN6001K

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250 \mu\text{A}$	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current at $V_{DS} = 60 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	-	± 5	μA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	V_{GSth}	0.8	-	2	V
Drain-Source On-State Resistance at $V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ at $V_{GS} = 4.5 \text{ V}, I_D = 0.2 \text{ A}$ at $V_{GS} = 2.5 \text{ V}, I_D = 0.05 \text{ A}$	$R_{DS(on)}$	- - -	- - 2.7	2 2.6 3.8	Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 10 \text{ V}, I_D = 200 \text{ mA}$	g_{fs}	-	307	-	mS
Gate resistance at $V_{DS} = 0 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	R_g	-	37	-	Ω
Input Capacitance at $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	29	-	pF
Output Capacitance at $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	10	-	pF
Reverse Transfer Capacitance at $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	7	-	pF
Total Gate Charge at $V_{DS} = 30 \text{ V}, I_D = 1 \text{ A}, V_{GS} = 10 \text{ V}$ at $V_{DS} = 30 \text{ V}, I_D = 1 \text{ A}, V_{GS} = 4.5 \text{ V}$	Q_g	- -	1.1 0.4	- -	nC
Gate to Source Charge at $V_{DS} = 30 \text{ V}, I_D = 1 \text{ A}, V_{GS} = 10 \text{ V}$	Q_{gs}	-	0.5	-	nC
Gate to Drain Charge at $V_{DS} = 30 \text{ V}, I_D = 1 \text{ A}, V_{GS} = 10 \text{ V}$	Q_{gd}	-	0.2	-	nC
Turn-On Delay Time at $V_{DD} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}, R_g = 6.8 \Omega$	$t_{d(on)}$	-	4.8	-	ns
Turn-On Rise Time at $V_{DD} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}, R_g = 6.8 \Omega$	t_r	-	3	-	ns
Turn-Off Delay Time at $V_{DD} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}, R_g = 6.8 \Omega$	$t_{d(off)}$	-	4.4	-	ns
Turn-Off Fall Time at $V_{DD} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}, R_g = 6.8 \Omega$	t_f	-	15	-	ns
Body-Diode PARAMETERS					
Diode Forward Voltage at $I_s = 0.3 \text{ A}, V_{GS} = 0 \text{ V}$	V_{SD}	-	-	1.5	V
Body-Diode Continuous Current	I_s	-	-	440	mA
Body Diode Reverse Recovery Time at $I_s = 1 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	t_{rr}	-	8.4	-	ns
Body Diode Reverse Recovery Charge at $I_s = 1 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	Q_{rr}	-	3.6	-	nC



Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

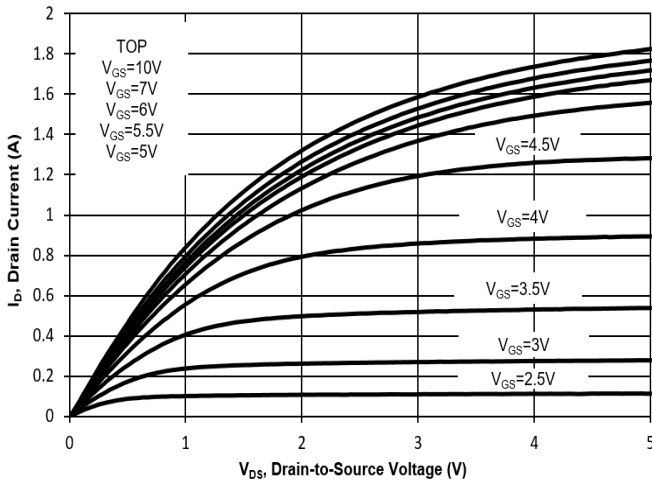


Fig. 2 Typical Transfer Characteristics

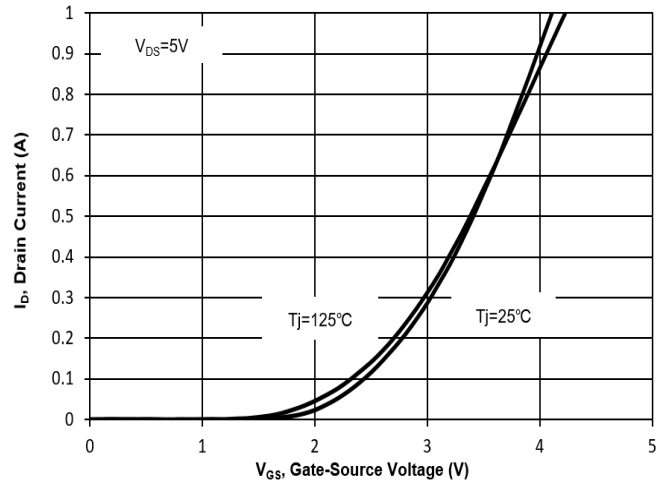


Fig. 3 on-Resistance vs. Drain Current

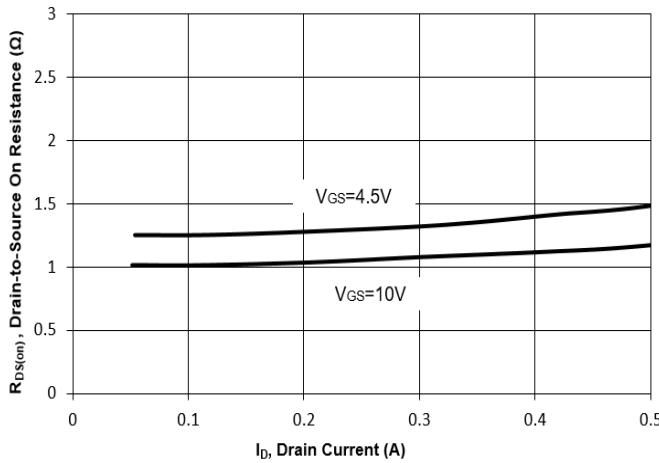


Fig. 4 on-Resistance vs. Gate-Source Voltage

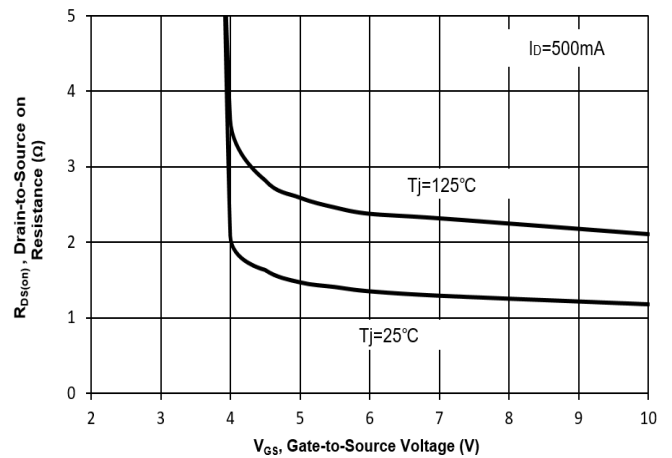


Fig. 5 on-Resistance vs. Tj

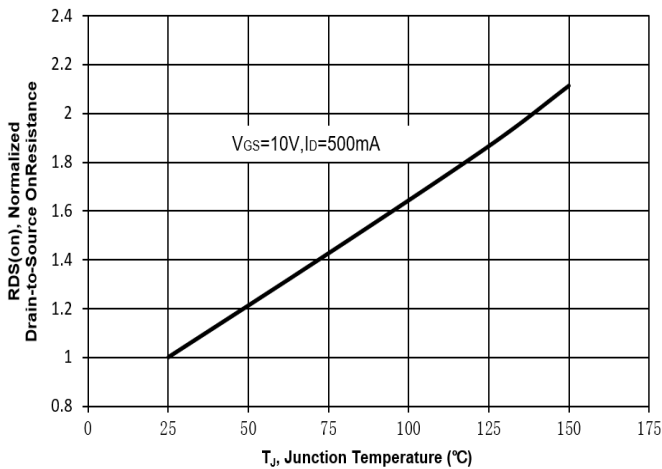
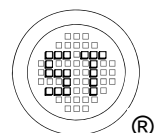
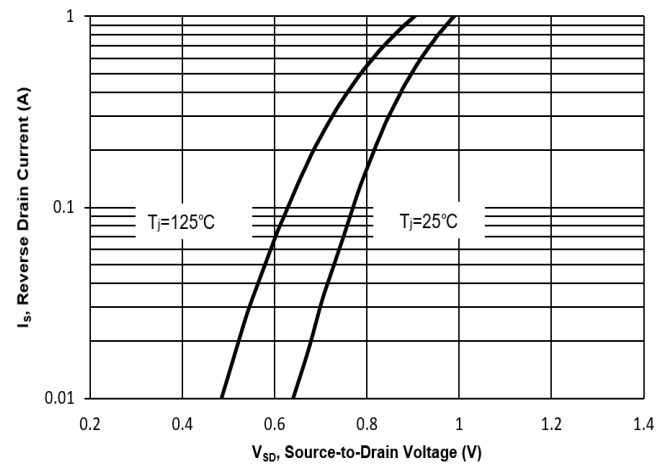


Fig. 6 Typical Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

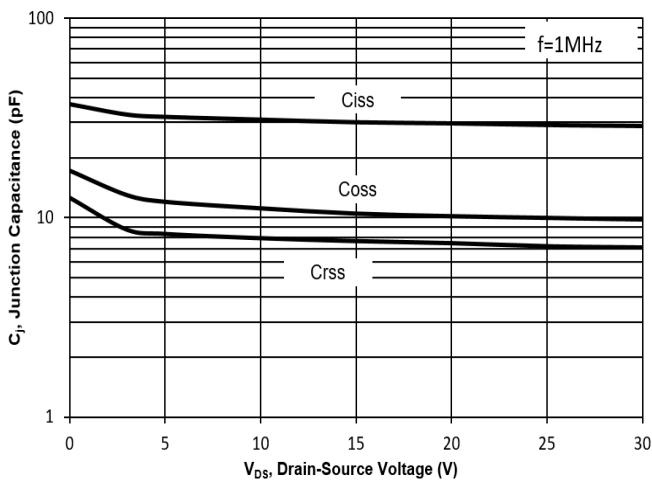


Fig. 8 Drain-Source Leakage Current vs. T_j

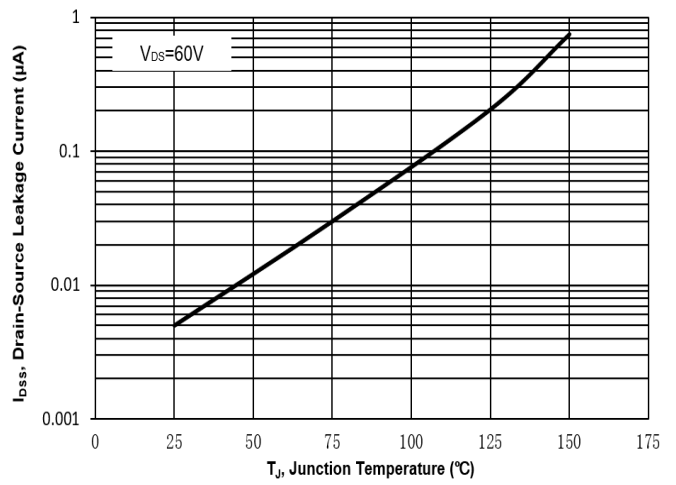


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

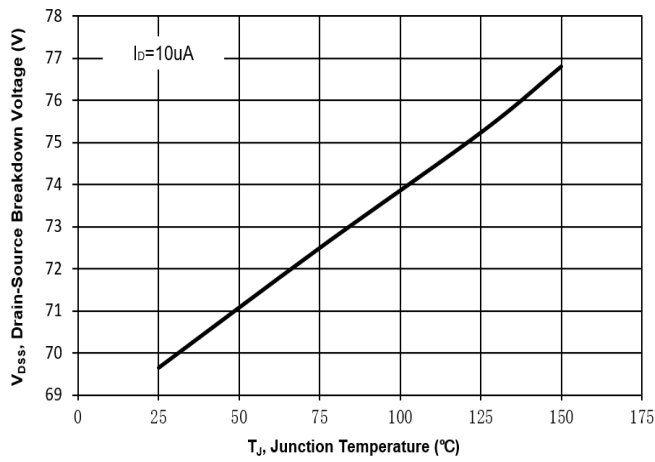


Fig. 10 Gate-Source Threshold Variation vs. T_j

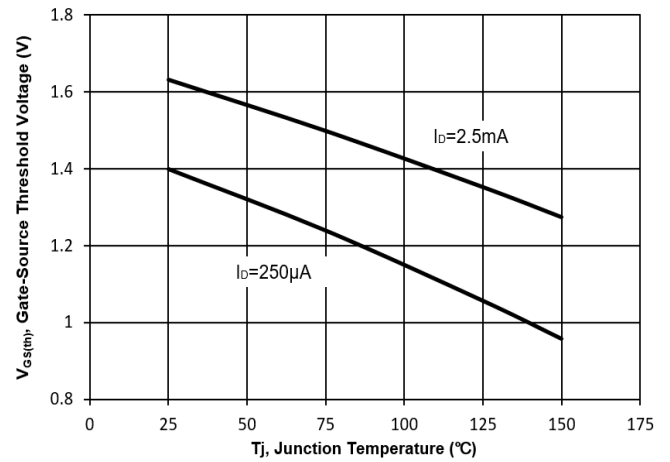
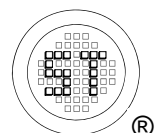
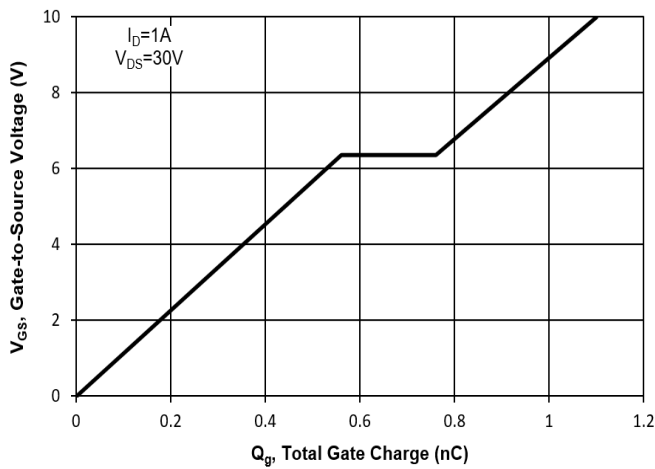


Fig. 11 Gate Charge



Test Circuits

Fig.1-1 Switching times test circuit

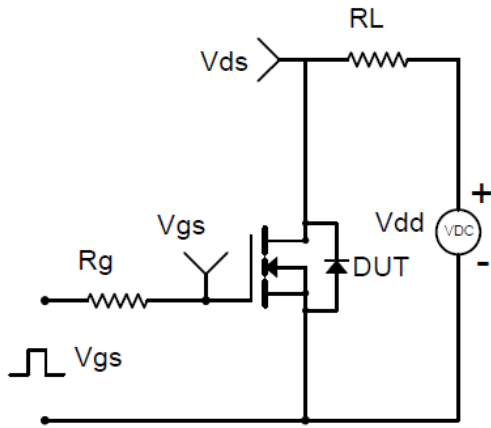


Fig.1-2 Switching Waveform

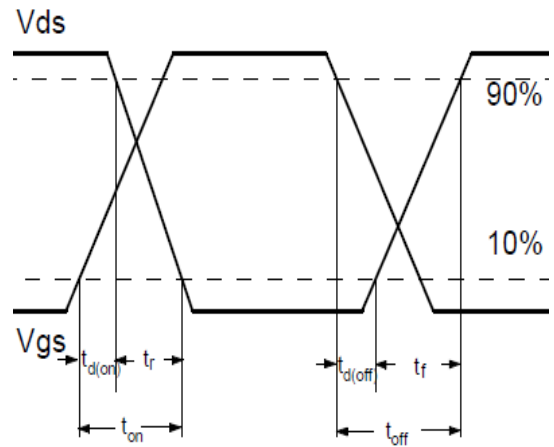


Fig.2-1 Gate charge test circuit

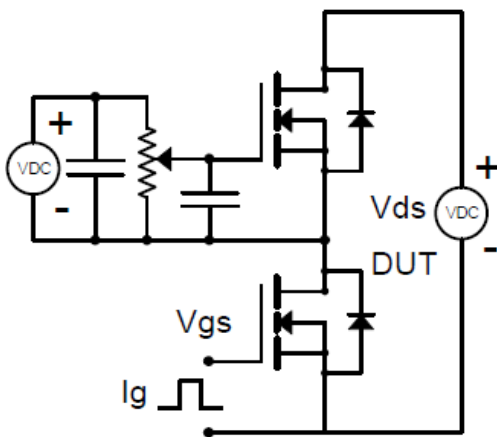
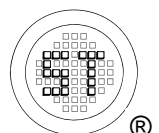
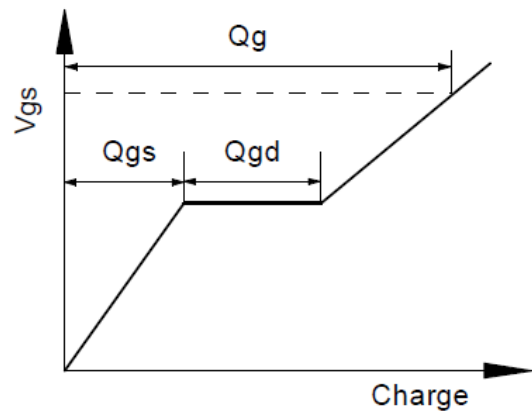


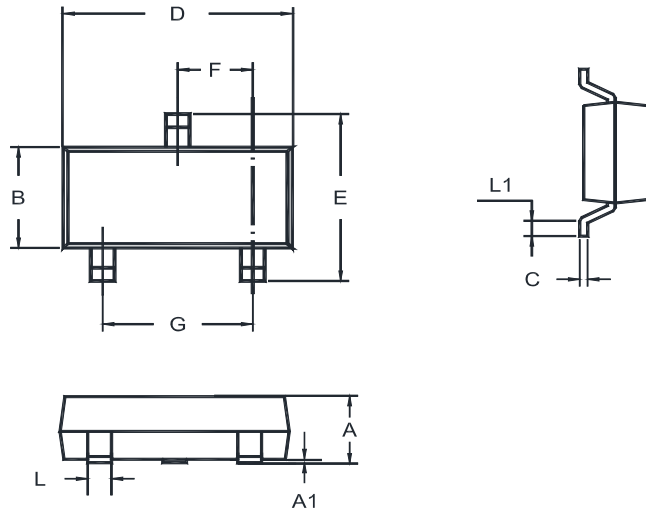
Fig.2-2 Gate charge waveform



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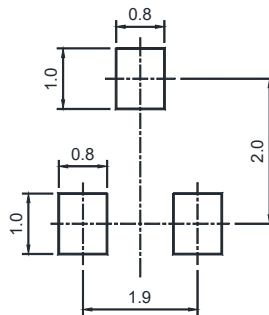
Package Outline (Dimensions in mm)

SOT-23



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

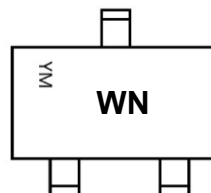
" WN " = Part No.

" YM " = Date Code Marking

" Y " = Year

" M " = Month

Font type: Arial



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